



Docket No.: M4065.0051/P051-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#25/G
3/13/13
Suresh

In re Patent Application of:
Leonard Forbes, et al.

Application No.: 09/609,813

Group Art Unit: 2815

Filed: July 3, 2000

Examiner: P. Brock, II

For: HIGH DENSITY PLANAR SRAM CELL
USING BIPOLAR LATCHUP AND GATED
DIODE BREAKDOWN

AMENDMENT

Box Non-Fee Amendment

Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated November 26, 2002 (Paper No. 23),
please amend the above-identified U.S. patent application as follows:

In the Claims:

Please rewrite claims 48, 55 and 62 as follows:

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48. (Four Times Amended) A method of forming a circuit for storing
information as one of at least two possible stable current states, the method comprising the
following steps:

providing a semiconductor substrate;

providing doped silicon regions to form a multi-region planar thyristor having at
least four regions;